

This Sheet Has Been Replaced



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ABSTRACT

The present invention relates to a plasma processing method and apparatus for generating a plasma with microwaves to subject a substrate to be treated such as a wafer to a plasma processing such as an etching or filming treatment.

In the plasma processing method and apparatus comprising: radiating microwave from the slot antenna which set at the bottom of resonator; generating plasma by using the microwave; and processing the sample by the plasma, the plasma of a ring-form is generated by the microwave radiated from the slot antennas which is disposed at an angle neither in parallel to nor perpendicular to a surface current to flow on a slot antenna plate. Thereby, the sample is uniformly processed.